

FIG. 1

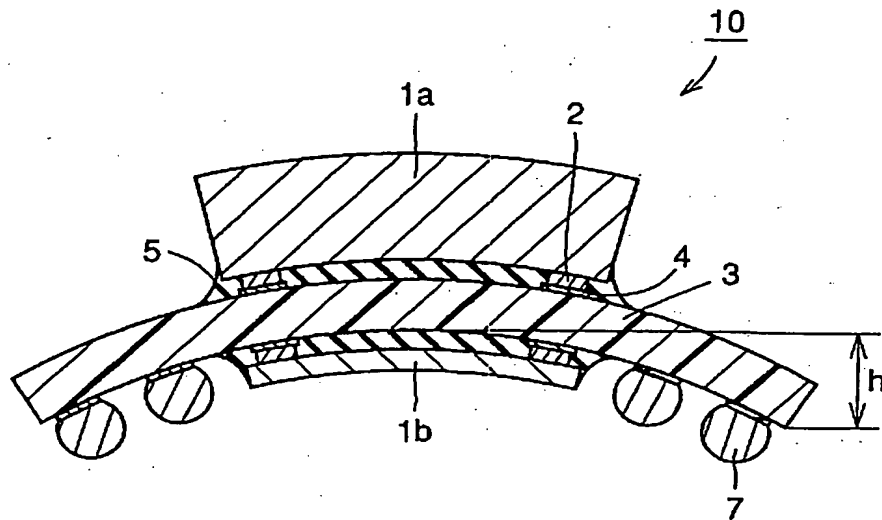


FIG. 2

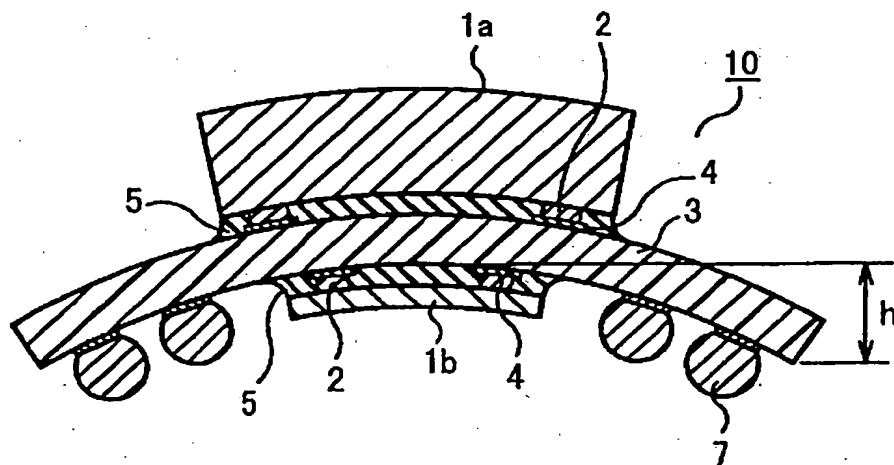


FIG. 3

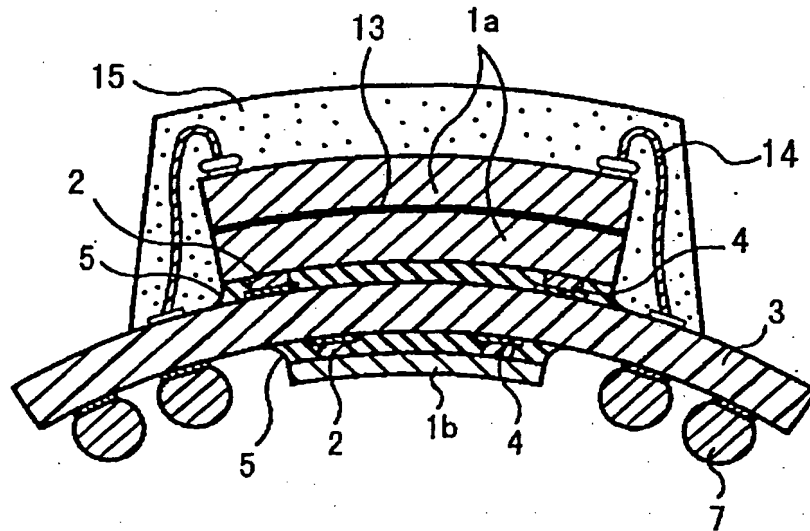


FIG. 4

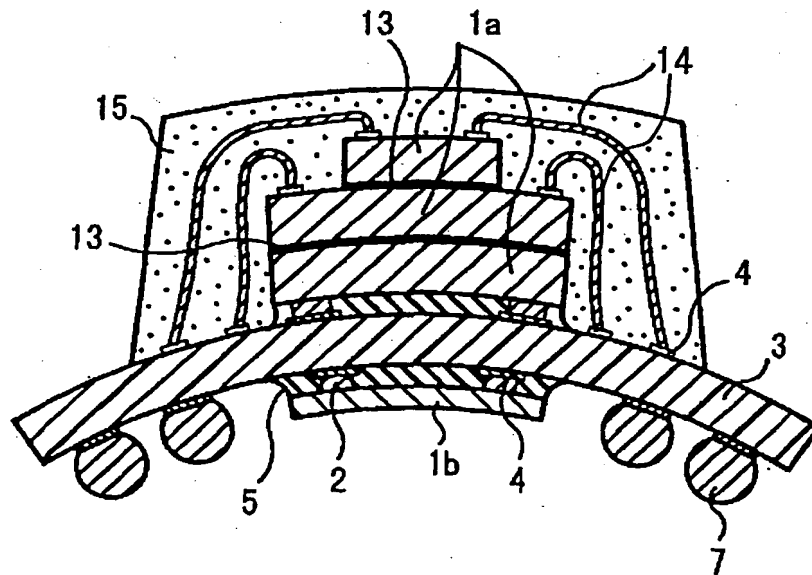


FIG. 5

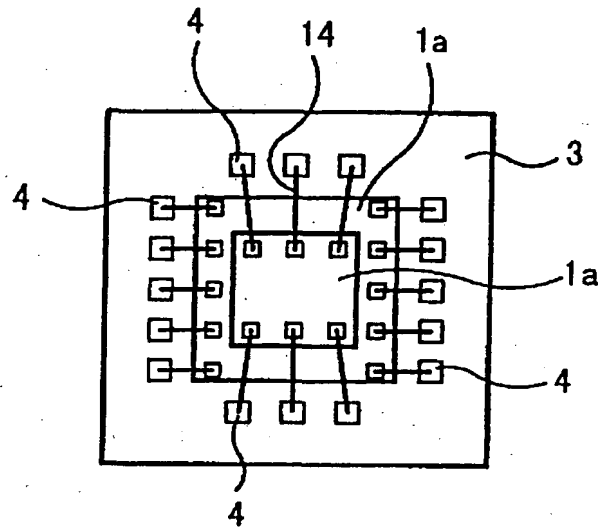


FIG. 6

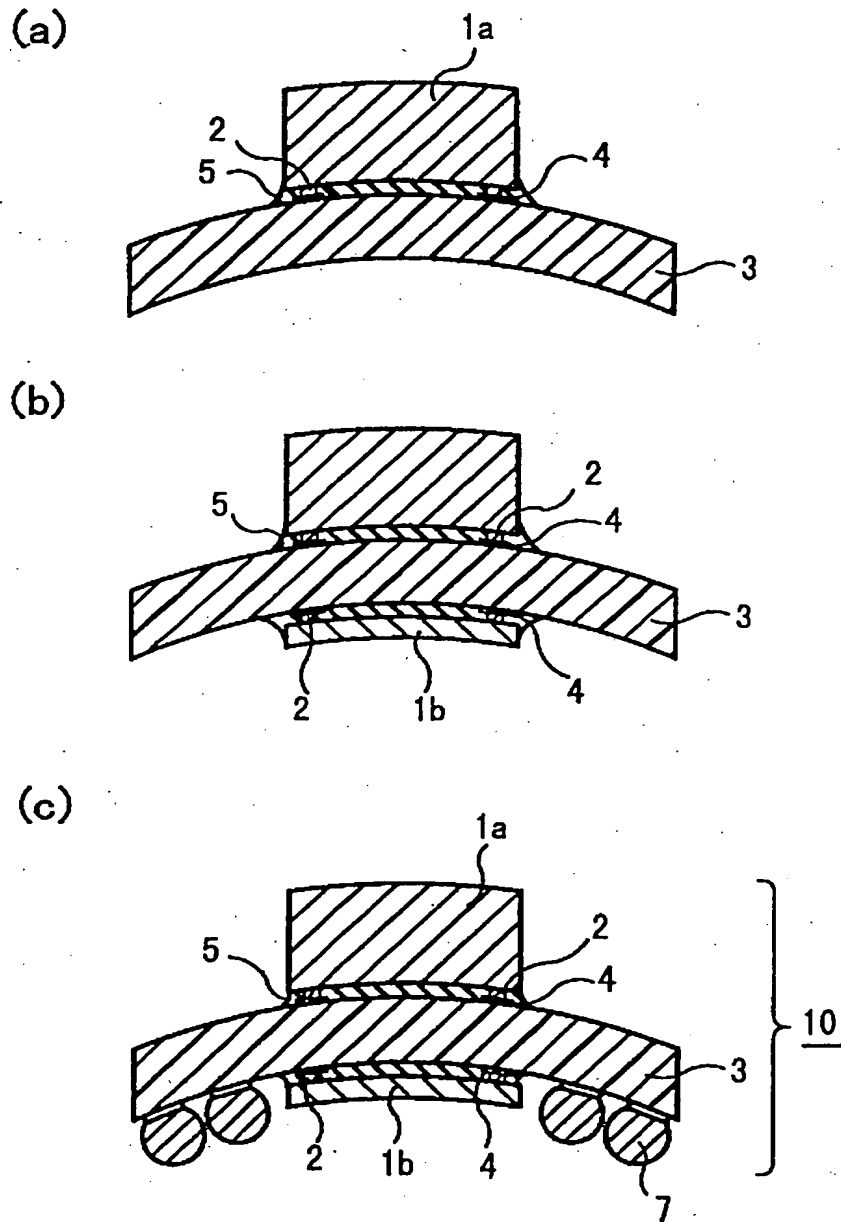
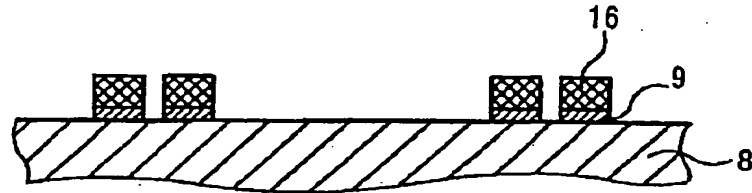
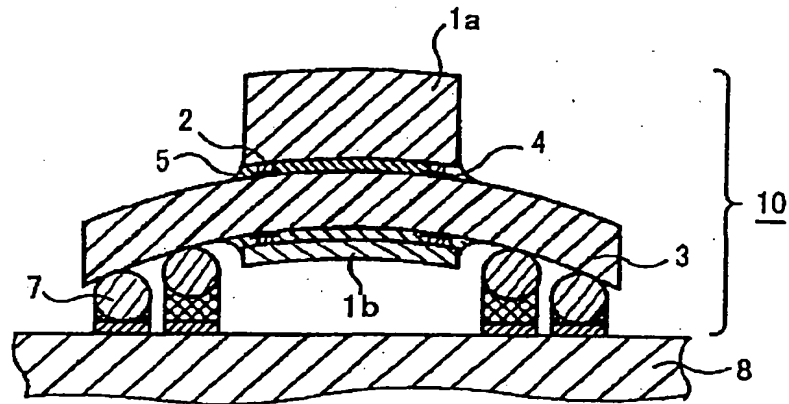


FIG. 7

(a)



(b)



(c)

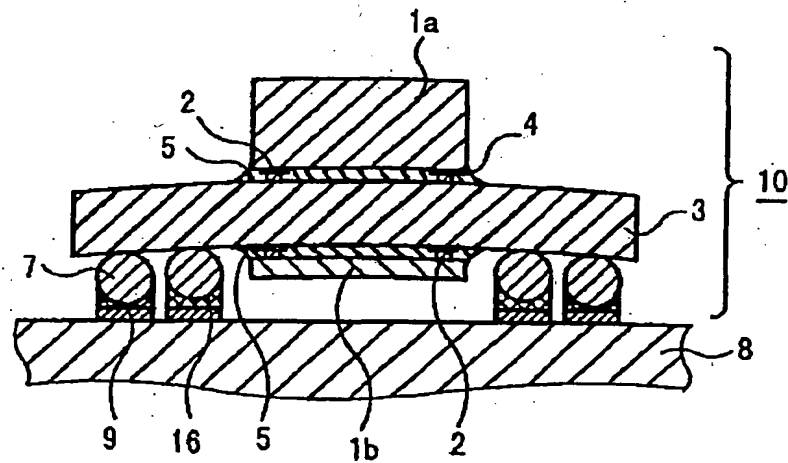


FIG. 8

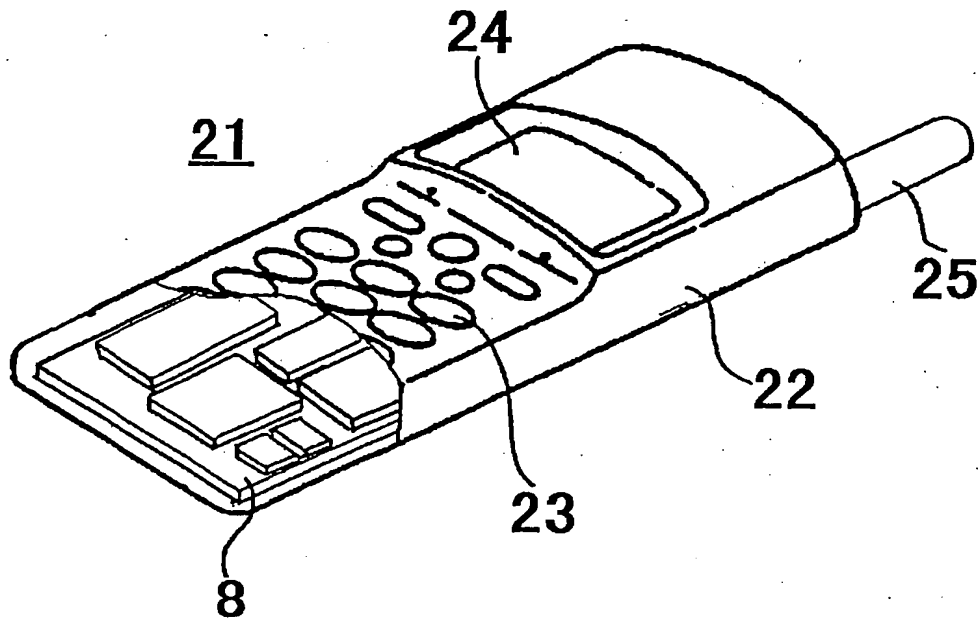


FIG. 9

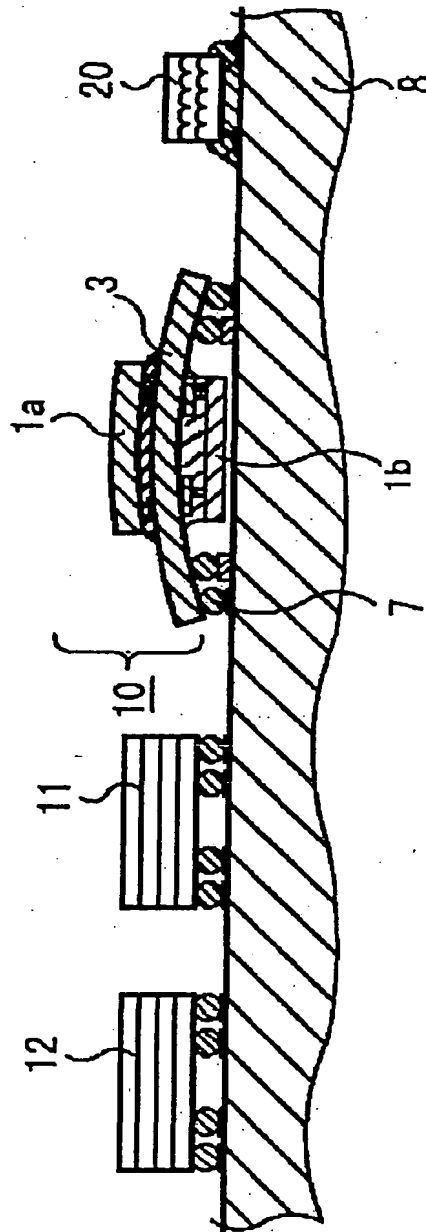
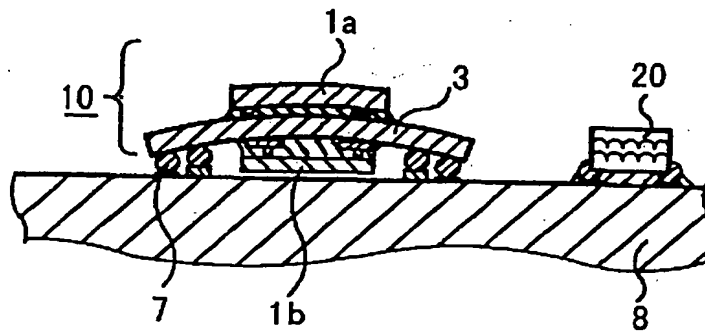


FIG. 10



This cross-sectional view shows a semiconductor device with a central channel 101b. The channel is flanked by two main regions, 101a on the left and 101b on the right. The left region 101a contains a stack of layers: 105 (top), 104, 104, and 102. The right region 101b contains a stack of layers: 108, 109, 107, 106, 116, 107, 104, 103, and 107. The central channel 101b is defined by a central layer 102. The device is shown in a cross-sectional view, with various layers and structures labeled with reference numerals.

FIG. 12 PRIOR ART

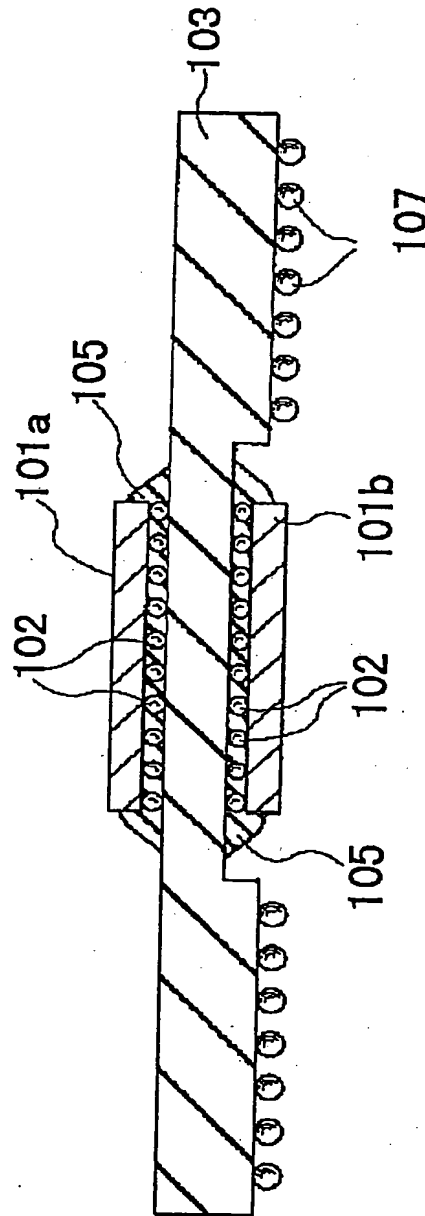


FIG. 13 PRIOR ART

